

AMENDMENTS TO THE CLAIMS:

1. (Cancel)
2. (Currently amended) A method of wire bonding ~~capillary~~ as claimed in claim 4 ~~[[1]]~~, wherein the angle of inclination of the face surface is in a range from 8° to 12°.
3. (Cancel)
4. (Currently amended) A method of wire bonding including steps of bonding wire to an external electrode and then bonding the wire to a top-surface electrode of a semiconductor device,

 ~~wherein a capillary as claimed in claim 1 is used to perform wire bonding is performed by use of a capillary having a face surface formed at a tip end thereof, the face surface inclining toward a center thereof so as to have a tapered shape, the capillary having a through hole formed therethrough so as to permit wire to be placed therethrough, the through hole having an opening at the center of the face surface,~~

 wherein an angle of inclination of the face surface relative to a plane perpendicular to an axis of the capillary and including the opening of the through hole is in a range from 4° to 15°, and a height of the face surface along the axis of the capillary is equal to or greater than a thickness of the wire, and

 wherein, when seen in a side sectional view including the axis of the capillary, a width of the face surface in a direction perpendicular to the axis of the capillary is greater than a width of the semiconductor device.
5. (Original) A method of wire bonding as claimed in claim 4, wherein a load applied to the capillary when the wire is pressed and deformed with the face

surface of the capillary so as to bond to the top-surface electrode of the semiconductor device is in a range from 100 to 200 g/cm².

6. (Previously presented) A method of wire bonding comprising:

bonding a first end of the wire to an external electrode using a capillary, the capillary having a face surface formed at a tip end, and inclining toward a center thereof, so as to have a tapered shape, the capillary also having a through hole to permit a wire to be placed therethrough, the through hole having an opening at the center of the face surface, and an angle of inclination of the face surface relative to a plane perpendicular to an axis of the capillary and including the opening of the through hole is in a range from 4 to 15; and

bonding a second end of the wire to a top-surface electrode of a semiconductor device using the capillary,

wherein the capillary, when seen in a side sectional view including the axis of the capillary, has a width of the face surface in a direction perpendicular to the axis of the capillary that is greater than a width of the semiconductor device.

7. (Previously presented) The method of claim 6, wherein the capillary has a height of the face surface along the axis of the capillary that is equal to or greater than a thickness of the wire.

8. (Previously presented) The method of claim 6, wherein the capillary has a uniform angle of inclination.